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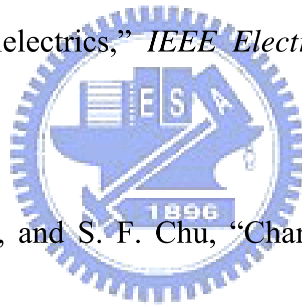

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論文題目：

高介電係數介電質在金氧金電容之研究

The Investigation of Metal-Insulator-Metal

Capacitor Using High-κ as Dielectrics

Publication List

(A) International Journal:

[1]. **K. C. Chiang**, J. W. Lin, H. C. Pan, C. N. Hsiao, W. J. Chen, H. L. Kao, I. J. Hsieh, and Albert Chin" Very High Density (44 fF/μm^2) $SrTiO_3$ MIM Capacitors for RF Applications," *Journal of the Electrochemical Society*, 154, H214 (2007). (This paper has also been selected for the February 5, 2007 issue of Virtual Journal of Nanoscale Science & Technology)

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